

IN THE CLAIMS

1. (Currently Amended) A ceramic heater to be used in semiconductor industry, comprising:

a disc-form ceramic substrate having a heating surface and comprising a nitride ceramic or a carbide ceramic;

a resistance heating element comprising at least one circuit, said resistance heating element being arranged on a an outermost surface of said ceramic substrate; and

an insulating covering deposited on the resistance heating element,

wherein said resistance heating element is positioned on an opposite side of said heating surface[[]]; and

said insulating covering comprises oxide glass with a thickness of 5 to 20 μm .

2. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 1,

wherein said insulating covering is deposited in a stretch containing a portion where said circuit is formed.

3-5. (Canceled)

6. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 1, wherein said insulating covering covers the resistance heating element comprising two or more circuits in a lump.

7-13. (Canceled)

14. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 2, wherein said insulating covering covers the resistance heating element comprising two or more circuits in a lump.

15-17. (Canceled)

18. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 1, further comprising a thermocouple.

19. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 18, wherein:

said ceramic substrate defines at least one through hole; and

said ceramic heater further comprises a lifter pin inserted through said through hole, said lifter pin being configured to support a semiconductor wafer at a distance above said ceramic substrate.

20. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 18, further comprising at least one bottom hole in a bottom surface of said ceramic substrate.

21. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 1,

wherein said resistance heating element is a metal or a conductive ceramic.

22. (Previously Presented) The ceramic heater to be used in semiconductor industry according to claim 1,

wherein said resistance heating element is a sintered body produced from metal particles or conductive ceramic particles.

23-29. (Canceled)

30. (New) The ceramic heater to be used in the semiconductor industry according to Claim 1, further comprising:

an insulating layer on the opposite side of said heating surface, wherein said resistance heating element is positioned on said insulating layer.